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10/735,695	12/16/2003	Glen Phillip Carey	11809/27	3546
23838 7.	590 12/02/2005		EXAMINER	
KENYON & KENYON			NGUYEN, TUAN H	
1500 K STREE	ET NW			
SUITE 700		ART UNIT	PAPER NUMBER	
WASHINGTO	N, DC 20005	2813		

DATE MAILED: 12/02/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

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Art Unit: 2813

DETAILED ACTION

Election/Restrictions

Applicant's election of Species I, claims 1-12 in the reply filed on 3/14/05 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Claim Rejections - 35 USC § 112

Claims 2, 3, 8, 9 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

In claim 2, it is unclear as to how could the doping level be controlled when there is no step of doping is recited.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

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Claims 1-5, 7-11 are rejected under 35 U.S.C. 102(e) as being anticipated by Yoshinaga et al..

Yoshinaga et al., figs. 1-9 and text on col. 5-10 disclose the claimed method for fabricating a semiconductor device including selecting a starting GaAs semiconductor substrate 1 having a defect density (GaAs wafer with low defect density is readily available from manufacturer); forming a single crystal semiconductor layer 2 of GaAs on the starting semiconductor substrate 1 by epitaxial growth method; forming active components 4 on the semiconductor layer 2 (col. 5, lines 15-to col. 7, line 60); removing the starting semiconductor substrate 1 (col. 7, last paragraph).

With respect to claims 2, 3, 8, 9, see col. 5, lines 35-42 for the step of controlling the doping level so as to attain an optimum result.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 6, 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshinaga et al..

Claims 6, 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yoshinaga et al. as applied to claims 1-5, 7-11 above, and further in view of Adomi et al..

Yoshinaga et al., in the method for fabricating a semiconductor device as explained above, fails to teach the formation of semiconductor layer from AlGaAsP.

Adomi, in a related method for forming a semiconductor device as shown in fig. 1 and text on col. 2, last paragraph, teaches the substitution of AlGaAs with AlGaAsP for forming a semiconductor layer on a GaAs substrate since it has very good lattice match with the GaAs, and the electrical and optical characteristics of AlGaAsP is not much different from those of AlGaAs.

Accordingly, it would have been obvious to one having ordinary skill I nthe art at the time the invention was made to have replaced AlGaAs with AlGaAsP for forming the semiconductor layer on GaAs substrate as suggested by Adomi et al. in Yoshinaga et al. process since the substitution of art recognized equivalence as suggested by Adomi et al. is within level of those skilled in the art.

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Maruska et al. discloses method for fabricating a semiconductor device on a temporary substrate and subsequently removing the substrate.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tuan H. Nguyen whose telephone number is 571-272-1694. The examiner can normally be reached on 9AM-5:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on 571-272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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> Tuan H. Nguyen Primary Examiner

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